

2SD1846

Silicon NPN Triple-Diffused Planar Type

Horizontal Deflection Output

■ Features

- Damper diode built-in
- Minimizes external component counts and simplifies circuitry
- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

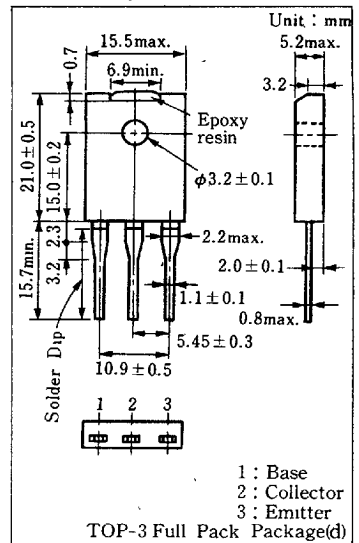
■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
Collector-emitter voltage	V _{CES}	1500	V
	V _{CEO}	700	V
Emitter-base voltage	V _{EBO}	7	V
Peak collector current	I _{CP}	10	A
Collector current	I _C	3.5	A
Base current	I _B	1.5	A
Collector power dissipation	P _C	60	W
		3	
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

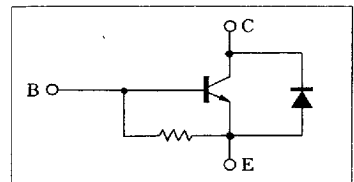
■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 750V, I _E = 0			10	μA
		V _{CB} = 1500V, I _E = 0			1	mA
Emitter-base voltage	V _{EBO}	I _E = 500mA, I _C = 0	7			V
DC current gain	h _{FE}	V _{CE} = 5V, I _C = 0.5A	5		25	
		V _{CE} = 10V, I _C = 3A	4			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 3A, I _B = 0.8A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 3A, I _B = 0.8A			1.5	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 0.5A, f = 0.5MHz		2		MHz
Storage time (L load)	t _{stg}	I _C = 3A, I _{B1} = 0.8A			8	μs
Collector current fall time (L load)	t _f	I _{B2} = -0.8A, L _{leak} = 5μH			0.8	μs
Storage time (R load)	t _{stg}	I _C = 3A, I _{B1} = 0.8A		1.5		μs
Collector current fall time (R load)	t _f	I _{B2} = -1.6A, V _{CC} = 200V		0.2		μs
Diode forward voltage	V _f	I _C = -3.5A, I _B = 0			2	V

■ Package Dimensions



■ Inner Circuit



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Panasonic

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